

OPA6423UR

Ultra Bright

Ultra Red LED Chip

AlGaInP /GaAs

1. Material Substrate GaAs (N Type)
 Epitaxial Layer AlGaInP (P/N Type)

2. Electrode N (Cathode) Side Gold Alloy
 P (Anode) Side Gold Alloy

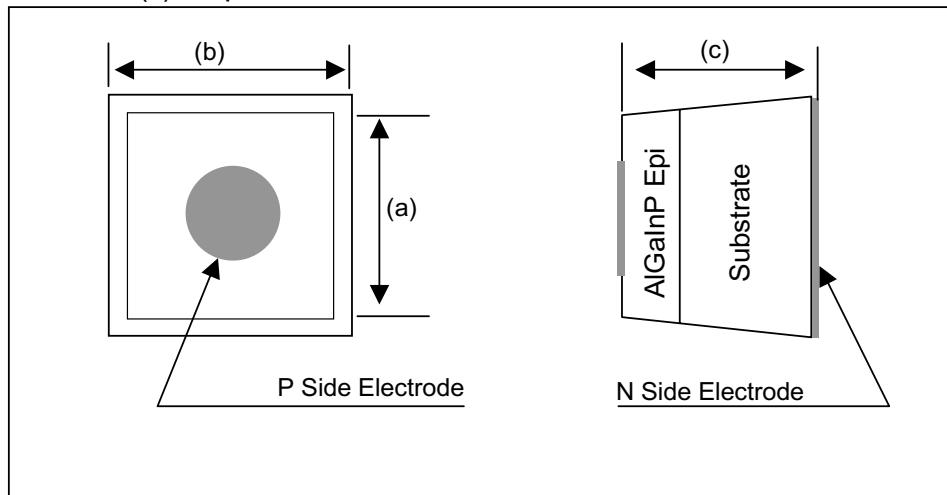
3. Electro-Optical Characteristics

| Parameter | Symbol | Min | Typ | Max | Unit | Condition |
|-----------------|-----------------|-----|-----|-----|------|----------------|
| Forward Voltage | $V_{F(1)}$ | | 1.7 | | V | $I_F=1mA$ |
| | $V_{F(2)}$ | | 2.1 | 2.4 | V | $I_F=20mA$ |
| Reverse Voltage | V_R | 6.0 | | | V | $I_R=100\mu A$ |
| Brightness | I_V | A | 14 | 20 | mcd | $I_F=20mA$ |
| | | B | 18 | 30 | | |
| | | C | 25 | 40 | | |
| | | D | 30 | 50 | | |
| | | E | 40 | 60 | | |
| | | F | 50 | 70 | | |
| Wavelength | λ_P | | 639 | | nm | $I_F=20mA$ |
| | λ_D | | 631 | | nm | $I_F=20mA$ |
| | $\Delta\lambda$ | | 20 | | nm | $I_F=20mA$ |

※ Note : Assembled into TO-18 Header without resin coating.

4. Mechanical Data

- (a) Emission Area ----- 8mil × 8mil
- (b) Bottom Area ----- 9mil × 9mil
- (c) Chip Thickness ----- 7mil



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